

LIGHTWAVE COMPONENTS & MODULES

AVALANCHE PHOTODIODES

Ge APDs

Part Number	Active area dia. (μm)	OPTICAL AND ELECTRICAL CHARACTERISTICS (T _a = 25°C)							Pack-age	Notes
		η (%)	f _c (GHz)	V _B (V)	I _D (nA)	I _{DM} ^{1*} (nA)	X ^{2*}	C _t (pF)		
		M=1 λ=1300nm	M=10 R _L =50Ω -3dB from 500kHz λ=1300nm	I _D =10μA	V _R =0.9VB	M=1	M=10 I _{PO} =2μA f=30MHz B=1MHz λ=1300nm	f=1MHz V _R =0.9VB		
FPD3R2LX	50	75	2.5	30	0.15	15	0.95	1.0	LX	With GI 50/125 micron MMF
FPD3R2KX	50	75	2.5	30	0.15	15	0.95	1.0	KX	With GI 50/125 micron MMF

InGaAs APDs

Part Number	Active area dia. (μm)	OPTICAL AND ELECTRICAL CHARACTERISTICS (T _a = 25°C)							Pack-age	Notes
		η (%)	f _c (GHz)	V _B (V)	I _D (nA)	I _{DM} ^{1*} (nA)	X ^{2*}	C _t (pF)		
		M=1 λ=1550nm	M=10 R _L =50Ω -3dB from 500kHz λ=1550nm	I _D =10μA	V _R =0.9VB	M=1	M=10 I _{PO} =2μA f=30MHz B=1MHz λ=1550nm	f=1MHz V _R =0.9VB		
FPD5W1KS	30	75	3	50	20	3	0.7	0.5	KS	With GI 50/125 micron MMF

1* Multiplied dark current

2* Excess noise factor (F) is expressed as F=M^X

FUJITSU